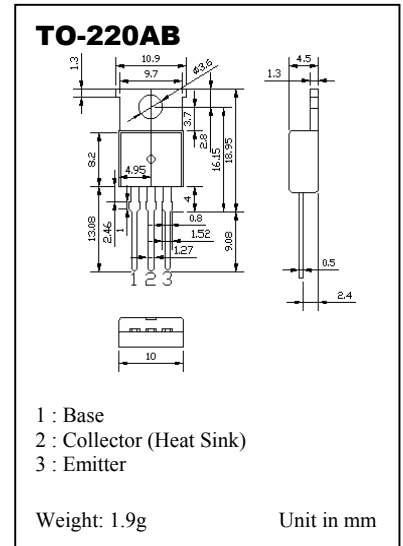


PNP SILICON EPITAXIAL POWER TRANSISTOR

... designed for power linear and switching applications.
 ... complementary to BD907.

MAXIMUM RATINGS

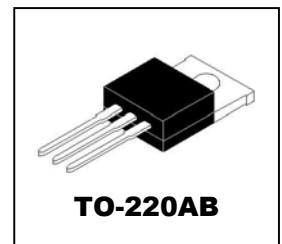
Characteristic	Symbol	Value	Unit
Collector Base Voltage (IE=0)	VCBO	-60	V
Collector Emitter Voltage (IB=0)	VCEO	-60	V
Emitter Base Voltage (IC=0)	VEBO	-5	V
Collector Current	IC, IE	-15	A
Base Current	IB	-5	A
Total Power Dissipation Tc≤25°C	Ptot	90	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-65 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Tc = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	ICBO	VCB=-60V, IE=0	-	-	-500	μA
Collector Cutoff Current	ICEO	VCB=-60V, IE=0, Tc=150°C	-	-	-5	mA
Collector Cutoff Current	ICEO	VCB=-30V, IB=0	-	-	-1	mA
Emitter Cutoff Current	IEBO	VEB=-5V, IC=0	-	-	-1	mA
DC Current Gain	hFE*	VCE=-4V, IC=-0.5A	40	-	250	-
		VCE=-4V, IC=-5A	15	-	150	-
		VCE=-4V, IC=-10A	5	-	-	-
Collector Emitter Saturation Voltage	VCE(sat)*	IB=-0.5A, IC=-5A	-	-	-1	V
		IB=-2.5A, IC=-10A	-	-	-3	V
Base Emitter Saturation Voltage	VBE(sat)*	IB=-2.5A, IC=-10A	-	-	-2.5	V
Base Emitter Voltage	VBE*	VCE=-4V, IC=-5A	-	-	-1.5	V
Collector Emitter Sustaining Voltage	VCE(sus)*	IB=0, IC=-100mA	-60	-	-	V
Transition Frequency	fT	VCE=-4V, IC=-0.5A	3	-	-	MHz

*Pulsed: Pulse duration=300μs, duty cycle1.5%.



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